

US Patent & Trademark Office

Patent Public Search | Text View

United States Patent Application Publication

20250267927

Kind Code

A1

Publication Date

August 21, 2025

Inventor(s)

Kakara; Hari Kishore et al.

FOLDED CASCODE LOW NOISE AMPLIFIER

Abstract

A disclosed low noise amplifier (LNA) includes a common-emitter amplifier (CE-A), a common-gate amplifier (CG-A) and various passive devices in CE-A and CG-A. CE-A includes an NPN-type bipolar junction transistor (BJT) with emitter and collector (E/C) regions and a base region between the E/C regions and connected to an input node. CG-A includes P-channel field effect transistor (PFET) with source and drain (S/D) regions, a channel region between the S/D region, and a gate adjacent to the channel region. The drain region of the PFET is connected to an output node. Additionally, a common inductor, collector region of the BJT, and source region of the PFET are connected at an intermediate node. The LNA is implemented on a three-dimensional integrated circuit (3DIC) with the BJT and FET on different chips and with passive devices in back end of the line regions between the BJT and FET.

Inventors: Kakara; Hari Kishore (AndhraPradesh, IN), Das; Indrajit (Bangalore, IN),
Vanukuru; Venkata Narayana Rao (Bangalore, IN)

Applicant: GlobalFoundries U.S. Inc. (Malta, NY)

Family ID: 1000007743467

Appl. No.: 18/583397

Filed: February 21, 2024

Publication Classification

Int. Cl.: H01L27/06 (20060101); **H01L27/12** (20060101); **H01L29/08** (20060101); **H01L29/10** (20060101); **H01L29/66** (20060101); **H03F3/213** (20060101)

U.S. Cl.:

CPC H10D84/401 (20250101); **H03F3/213** (20130101); **H10D10/021** (20250101); **H10D62/137** (20250101); **H10D62/177** (20250101); **H10D86/201** (20250101); H03F2200/177 (20130101); H03F2200/294 (20130101); H03F2200/451 (20130101)

Background/Summary

BACKGROUND

[0001] The present disclosure relates to amplifier circuits, and more particularly, to low noise amplifiers (LNAs).

[0002] LNAs are important for use in a variety of different applications. Ultra-low power LNAs are particularly important for use in satellite-based applications, such as global positioning systems (GPSs) and global navigation satellite systems (GNSs). An ultra-low power LNA can, for example, have a direct current (DC) power rating of approximately 2 mW. Ideally, such ultra-low power LNAs will exhibit high gain and high linearity (e.g., specified as a third order intercept point (IIP3)) without significantly degrading the noise factor (NF). Cascode LNAs (also referred to herein as multi-stage LNAs) that include bipolar junction transistor (BJT)-based amplifiers in each stage have developed for ultra-low power operation. However, these ultra-low power cascode LNAs tend to exhibit either high gain or high linearity, but not both.

SUMMARY

[0003] Disclosed herein are embodiments of a structure including a cascode LNA. The LNA can include a bipolar junction transistor (BJT). The BJT can include an emitter region, a collector region, and a base region between the emitter and collector regions. The base region of the BJT can further be connected to an input node. The LNA can also include a field effect transistor (FET). The FET can include a source region, a drain region, a channel region between the source and drain regions, and a gate adjacent to the channel region. The source region of the FET can be connected to the collector region of the BJT. Additionally, the drain region of the FET can be connected to an output node. In some embodiments of the disclosed structure, the BJT and FET can be on different chips of a three-dimensional integrated circuit (3DIC).

[0004] For example, a disclosed structure embodiment can include a cascode LNA. The LNA can include a BJT on a first chip. The BJT can include an emitter region, a collector region, and a base region between the emitter and collector regions. The base region of the BJT can further be connected to an input node. The LNA can further include a FET on a second chip that is stacked on the first chip. The FET can include a source region, a drain region, a channel region between the source and drain regions, and a gate adjacent to the channel region. The source region of the FET can be connected to the collector region of the BJT. Additionally, the drain region of the FET can be connected to an output node.

[0005] Another disclosed structure embodiment can similarly include a cascode LNA. In this case, the LNA can include a FET can be on a first chip and a BJT on a second chip that is stacked on the first chip. As in the previously described embodiments, the BJT can include an emitter region, a collector region, and a base region between the emitter and collector regions. The base region of the BJT can further be connected to an input node. Additionally, the FET can include a source region, a drain region, a channel region between the source and drain regions, and a gate adjacent to the channel region. The source region of the FET can be connected to the collector region of the

BJT.

[0006] It should be noted that all aspects, examples, and features of disclosed embodiments mentioned in the summary above can be combined in any technically possible way. That is, two or more aspects of any of the disclosed embodiments, including those described in this summary section, may be combined to form implementations not specifically described herein. The details of one or more implementations are set forth in the accompanying drawings and the description below. Other features, objects and advantages will be apparent from the description and drawings, and from the claims.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] The present disclosure will be better understood from the following detailed description with reference to the drawings, which are not necessarily drawn to scale and in which:

[0008] FIG. 1 is a schematic diagram illustrating disclosed embodiments of a low noise amplifier (LNA);

[0009] FIGS. 2 and 3 are cross-section diagrams illustrating examples of a BJT and a FET, respectively, that could be incorporated into the LNA of FIG. 1;

[0010] FIGS. 4A-1, 4A-2, 4B-1 and 4B-2 are layout diagrams illustrating examples of different inductors that could be incorporated into the LNA of FIG. 1;

[0011] FIGS. 5A-5B are layout diagrams illustrating examples of different capacitors that could be incorporated into the LNA of FIG. 1;

[0012] FIGS. 6A-6B are cross-section diagrams illustrating different three-dimensional integrated circuits (3DICs), respectively, including the LNA of FIG. 1; and

[0013] FIGS. 7.1-7.2 are cross-section diagrams illustrating a method of forming a 3DIC including the LNA of FIG. 1.

DETAILED DESCRIPTION

[0014] As mentioned above, ideally, ultra-low power LNAs will exhibit both high gain and high linearity without significantly degrading the noise factor (NF) (i.e., the ratio of the signal to noise ratio at the input to the signal to noise ratio at the output). Cascode LNAs (also referred to herein as multi-stage LNAs) that include BJT-based amplifiers in each stage have been developed for ultra-low power operation. However, these ultra-low power cascode LNAs tend to exhibit either high gain or high linearity, but not both.

[0015] In view of the foregoing, disclosed herein are embodiments of a cascode LNA (referred to hereinafter as the LNA). The LNA can include a common-emitter amplifier (CE-A) in an input stage (S1) and a common-gate amplifier (CG-A) in an output stage (S2). CE-A can include a bipolar junction transistor (BJT) (including an emitter region, a collector region, a base region between the emitter and collector regions) and various passive devices connected to the BJT. Additionally, the base region of the BJT can be connected to an input node for receiving a radio frequency input signal (RFin). The BJT can be, for example, an NPN-type BJT with the base region including silicon germanium (SiGe). CG-A can include a field effect transistor (FET) (including a source region, a drain region, a channel region between the source region and the drain region, and a gate adjacent to the channel region) and various passive devices connected to the FET.

Additionally, the source region of the FET can be connected to the collector region of the BJT and the drain region of the FET can be connected to an output node for outputting a radio frequency output signal (RFout). The FET can be, for example, a P-channel FET (PFET) having a silicon active device region. In some embodiments, the LNA can be included in a three-dimensional integrated circuit (3DIC). In this case, the BJT of CE-A and FET of CG-A can be on different chips of the 3DIC and various passive devices of the two amplifiers can be contained within the

interlayer dielectric (ILD) material and back end of the line (BEOL) metal levels that separate the BJT and FET. The LNA can operate at low power or even ultra-low power (e.g., with a DC power rating of approximately 2 milliwatts (mW)) and can exhibit relatively high gain (e.g., at or above 20 decibels (dB)), relatively high linearity (e.g., specified as a third order intercept point (IIP3) at or above -12 decibel-milliwatts (dBm)) and a noise factor (NF) of 0.5 dB to 1.0 dB (e.g., an NF of 0.7 dB). As compared to known ultra-low power cascode LNAs (e.g., that include only BJTs), the LNA may exhibit only a minimal reduction in gain, essentially no change in NF, and a beneficial significant increase in linearity (e.g., in IIP3).

[0016] FIG. 1 is a schematic diagram illustrating disclosed embodiments of a LNA **100**. The LNA **100** can be a cascode LNA. That is, it can include multiple stages and, particularly, an input stage (S1) and an output stage (S2) electrically connected to S1. S1 can include a common-emitter amplifier (CE-A). The CE-A can include a bipolar junction transistor (BJT) **110** and first passive devices (including, for example, inductors **115** and **117** and capacitor **116**) connected to BJT **110**. S2 can include a common-gate amplifier (CG-A) including a field effect transistor (FET) **120** and second passive devices (including, for example, an inductor **125**, capacitors **127** and **128**, and a resistor **126**) connected to FET **120**. S1 and S2 can also share a common inductor **130**, which is connected to both BJT **110** of CE-A and FET **120** of CG-A. BJT **110** of CE-A can specifically be an NPN-type BJT, whereas FET **120** of CG-A can specifically be a P-channel FET (PFET).

[0017] FIG. 2 is a cross-section diagram illustrating an example of an NPN-type BJT **110** that could be incorporated into CE-A. The example NPN-type BJT **110** shown in FIG. 2 is a semiconductor-on-insulator, symmetric, lateral, NPN-type heterojunction bipolar transistor (HBT) (also referred to herein as a SiGe NPN-type BJT).

[0018] Specifically, in this example, NPN-type BJT **110** is on an insulator layer **204**. Insulator layer **204** can be, for example, a silicon dioxide layer or a layer of any other suitable insulator material. At least during processing, insulator layer **204** can be on a monocrystalline semiconductor substrate (e.g., a monocrystalline silicon substrate or a monocrystalline substrate of any other suitable semiconductor material).

[0019] NPN-type BJT **110** can include an active device region defined in a semiconductor layer **205** on insulator layer **204**. Semiconductor layer **205** can be a first semiconductor material (e.g., monocrystalline Si). The shape of the active device region can be defined by isolation regions **206** (e.g., shallow trench isolation (STI) regions) that extend through semiconductor layer **205** at least to and, optionally, into or through insulator layer **204**.

[0020] NPN-type BJT **110** can include an emitter region **111** and a collector region **112** with N-type conductivity. NPN-type BJT **110** can further include a base region **113** positioned laterally between emitter and collector regions **111** and **112** and having P-type conductivity. More specifically, emitter and collector regions **111** and **112** can include N-doped regions **111.1** and **112.1**, respectively, of semiconductor layer **205**. Optionally, emitter and collector regions **111** and **112** can further include N-doped monocrystalline epitaxial semiconductor layers **111.2** and **112.2** of the first semiconductor material (e.g., Si) above and immediately adjacent to regions **111.1** and **112.1**, respectively. As illustrated, the emitter and collector regions **111** and **112** can be essentially symmetric.

[0021] In a standard BJT, base region **113** would, like emitter and collector regions **111** and **112**, be made of the first semiconductor material (e.g., Si). In this example, the BJT is more specifically an HBT. That is, base region **113** can include, at least in part, a second semiconductor material (e.g., silicon germanium (SiGe)) that is different from the first semiconductor material (e.g., Si). Those skilled in the art will recognize that the use of differing semiconductor materials at the emitter-base junction and at base-collector junction creates heterojunctions suitable for handling higher frequencies. Thus, for example, base region **113** can include an undoped or P-doped region **113.1** of semiconductor layer **205** positioned laterally between N-doped regions **111.1** and **112.1** of emitter and collector regions **111** and **112**. Optionally, semiconductor layer **205** can be recessed at region

113.1 so that region **113.1** is shorter in height than adjacent regions **111.1** and **112.1**. Region **113.1** can function, during processing, as a seed layer for growth of additional epitaxial layers of base region **113**. That is, base region **113** can further include an undoped or P-doped epitaxial semiconductor layer **113.2** of the second semiconductor material (e.g., SiGe) on region **113.1**. This epitaxial semiconductor layer **113.2** can, for example, be selectively grown on region **113.1** so that it is monocrystalline in structure and so that it fills a relatively narrow lower base opening, which is defined by a space between first sidewall spacers **215**. As illustrated, first sidewall spacers **215** can be multi-layered. Base region **113** can further include a P-doped epitaxial semiconductor layer **113.3** of the first or second semiconductor materials (e.g., Si or SiGe) above and immediately adjacent to epitaxial semiconductor layer **113.2**. This epitaxial layer **113.3** can, for example, be non-selectively grown such that it is polycrystalline in structure. Additionally, it can extend laterally over first sidewall spacers **215** so as to be wider than epitaxial semiconductor layer **113.2** and it can have vertical sidewalls. Additional first sidewall spacers **216** can be positioned laterally adjacent to the vertical sidewalls so as to isolate epitaxial semiconductor layer **113.3** of base region **113** from epitaxial semiconductor layers **111.2** and **112.2** of emitter and collector regions **111** and **112**, respectively.

[0022] It should be understood that the example NPN-type BJT **110** shown in FIG. 2 is provided for illustration purposes and is not intended to be limiting. Alternatively, the NPN-type BJT **110** incorporated into CE-A of LNA **100** could have any other suitable configuration. For example, NPN-type BJT **110** could be a bulk semiconductor structure as opposed to a semiconductor-on-insulator structure (as illustrated), NPN-type BJT **110** could be a standard BJT as opposed to an HBT (as illustrated), NPN-type BJT **110** could be a vertical device as opposed to a lateral device (as illustrated), NPN-type BJT **110** could be an asymmetric device as opposed to a symmetric device (as illustrated), etc. In any case, as illustrated in FIG. 1, NPN-type BJT **110** includes at least emitter and collector regions **111** and **112** and a base region **113** positioned between emitter and collector regions **111** and **112**.

[0023] Referring again to FIG. 1, CE-A can further include various first passive devices electrically connected to BJT **110**. The first passive devices can include, but are not limited to, inductors **115** and **117** and capacitor **116**, as illustrated. Specifically, CE-A can include an emitter inductor **115** electrically connected at opposite end terminals to emitter region **111** and to ground **198**. CE-A can further include a base inductor **117** electrically connected at opposite end terminals to an input node **101** (which receives a radio frequency input signal (RFin)) and to base region **113**. CE-A can further include an emitter-base capacitor **116**, which has a pair of conductive plates that are separated by a capacitor dielectric and which are electrically connected to emitter region **111** and to base region **113**, respectively. It should be noted that another inductor (referred to herein as common inductor **130** because it is common to both S1 and S2) has opposite end terminals electrically connected to a positive voltage rail **199** for receiving a positive supply voltage (VCC) and electrically connected to an intermediate node **104** and thereby to collector region **112** (as well as to FET **120**, as discussed further below).

[0024] FIG. 3 is a cross-section diagram illustrating an example of a FET **120** that could be incorporated into CG-A as FET **120**. FET **120** shown in FIG. 3 is a semiconductor-on-insulator, symmetric, planar, P-channel FET (PFET).

[0025] Generally, in this example, PFET **120** is on an insulator layer **304**. Insulator layer **304** can be, for example, a silicon dioxide layer or a layer of any other suitable insulator material. At least during processing, insulator layer **304** can be on a monocrystalline semiconductor substrate (e.g., a monocrystalline silicon substrate or a monocrystalline substrate of any other suitable semiconductor material).

[0026] PFET **120** can include an active device region defined in a semiconductor layer **305** on insulator layer **304**. Semiconductor layer **305** can be a first semiconductor material (e.g., monocrystalline Si). The shape of the active device region can be defined by isolation regions **306**

(e.g., shallow trench isolation (STI) regions) that extend through semiconductor layer **305** at least to and, optionally, into or through insulator layer **304**.

[0027] PFET **120** can include source and drain regions **121** and **122** with P-type conductivity, a channel region **123** positioned laterally between source and drain regions **121** and **122** and having P-type conductivity, and a gate **124** adjacent to the channel region **123**. More specifically, source and drain regions **121** and **122** can include P-doped regions **121.1** and **122.1**, respectively, of semiconductor layer **305**. Optionally, source and drain regions **121** and **122** can further include P-doped monocrystalline epitaxial semiconductor layers **121.2** and **122.2** (also referred to herein as raised source and drain regions) of the first semiconductor material (e.g., Si) above and immediately adjacent to regions **121.1** and **122.1**, respectively. As illustrated, the source and drain regions **121** and **122** can be essentially symmetric. Channel region **123** can include a region of semiconductor layer **305** positioned laterally between P-doped regions **121.1** and **122.1** of source and drain regions **121** and **122**. Channel region **123** can be either undoped (i.e., an intrinsic channel region) or doped so as to have N-type conductivity at a relatively low conductivity level. Gate **124** can include a gate dielectric layer **124.1** (including one or more layers of gate dielectric material) on the top surface of semiconductor layer **305** at channel region **123**) and a gate conductor layer **124.2** (including one or more layers of gate conductor material on the gate dielectric layer **124.1**). Gate **124** can be, for example, a gate first gate high-K metal gate structure or any other suitable gate structure. Gate sidewall spacers **315** can electrically isolate gate **124** from source and drain regions **121** and **122**.

[0028] PFET structures as described above are well known in the art and, thus, more specific details thereof (including additional features that may be incorporated into such a PFET) have been omitted from the specification in order to allow the reader to focus on the salient aspects of the disclosed embodiments related to inclusion generally of a PFET in CG-A of LNA **100**, as illustrated in FIG. **1**. Furthermore, it should be understood that the configuration of the PFET **120** shown in FIG. **3** is provided for illustration purposes and is not intended to be limiting. Alternatively, PFET **120** incorporated into CG-A of LNA **100** could have any other suitable configuration. For example, PFET **120** could be a bulk semiconductor structure as opposed to a semiconductor-on-insulator structure (as illustrated), a non-planar PFET as opposed to a planar PFET (as illustrated), a multi-gate finger PFET as opposed to a single gate PFET (as illustrated), an asymmetric PFET as opposed to a symmetric PFET (as illustrated), etc. In any case, as illustrated in FIG. **1**, PFET **120** includes a source and drain regions **121** and **122**, a channel region **123** between source and drain regions **121** and **122**, and a gate **124** adjacent to the channel region **123**. Various different PFET structures are well known in the art and could instead be incorporated into CG-A of LNA **100**.

[0029] Referring again to FIG. **1**, source region **121** of PFET **120** can be electrically connected to collector region **112** of NPN-BJT **110** and to common inductor **130** at intermediate node **104**. CG-A can further include various second passive devices electrically connected to PFET **120**. The second passive devices can include, but are not limited to, an inductor **125**, capacitors **127** and **128**, and a resistor **126**, as illustrated. Specifically, CG-A can include a drain inductor **125** electrically connected at opposite end terminals to drain region **122** and to ground **198**. CG-A can further include a gate capacitor **127**, which has a pair of conductive plates that are separated by a capacitor dielectric and which are electrically connected to gate **124** and to ground **198**, respectively. CG-A can further include an output capacitor **128**, which has a pair of conductive plates that are separated by a capacitor dielectric and which are electrically connected to drain region **122** and to an output node **102**, respectively. A radio frequency output signal (RFout) can be output at output node **102** in response to RFin received at input node **101**. CG-A can further include a resistor **126** (also referred to herein as a gate resistive element) with opposing end terminals electrically connected to gate **124** and to a bias voltage node **103** (e.g., for receiving a bias voltage (Vcas)).

[0030] An inductor refers to a two-terminal electronic device that stores energy in a magnetic field when current flows through the device. An inductor typically includes an insulated wire wound in a

spiral or coil shape. Within an IC, inductors can be formed in back end of the line (BEOL) metal levels and electrically connected to front end of the line (FEOL) devices (e.g., BJTs, FETs, etc.) via interconnects (including, for example, middle of the line (MOL) contacts and BEOL vias and/or wires). FIGS. 4A-1, 4A-2, 4B-1 and 4B-2 are layout diagrams illustrating examples of BEOL spiral-shaped planar inductors that could be incorporated into CE-A and CG-A or as common inductor **130**. Specifically, FIGS. 4A-1 illustrates hexagon spiral-shaped planar inductor where the BEOL wire is patterned to have a uniform width from one end to the other. FIGS. 4A-2 illustrates hexagon spiral-shaped planar inductor where the BEOL wire is patterned to have a tapering width from an outside end to an inside end at the center of the spiral. FIGS. 4B-1 illustrates square spiral-shaped planar inductor where the BEOL wire is patterned to have a uniform width from one end to the other. FIGS. 4B-2 illustrates square spiral-shaped planar inductor where the BEOL wire is patterned to have a tapering width from an outside end to an inside end at the center of the spiral. The hexagon and square shapes of the spiral inductors illustrated in FIGS. 4A-1 and 4A-2 and in FIGS. 4B-1 and 4B2, respectively, are provided for illustration purposes. Alternatively, any other suitable spiral shape could be employed (e.g., circular, etc.). A capacitor refers to another two-terminal electronic device that stores energy in an electric field by accumulating charges on oppositely charged conductive plates insulated from each other by a capacitor dielectric. Within an IC, capacitors can be formed in BEOL metal levels and electrically connected to FEOL devices (e.g., BJTs, FETs, etc.) via interconnects (including, for example, MOL contacts and BEOL vias and/or wires). FIGS. 5A and 5B are layout diagrams illustrating examples of BEOL conventional plate and interdigitated capacitors that could be incorporated into CE-A and CG-A of LNA **100**. A resistor is a two-terminal electronic device that provide resistance to current flow (e.g., to bias active elements, adjust signal levels, etc.). Within an IC, resistors can be formed in BEOL metal levels (e.g., thin film resistors), as MOL structures (e.g., polysilicon resistors), or even as FEOL structures (e.g., silicon resistors). The passive devices mentioned above and included within LNA **100** could have any now known or subsequently developed configuration.

[0031] In embodiments disclosed herein, LNA **100** can be implemented on a three-dimensional integrated circuit (3DIC). FIGS. 6A and 6B are cross-section diagrams illustrating embodiments of LNA **100** implemented on a 3DIC structure **600A** and **600B**, respectively. In each of these embodiments, 3DIC structure **600A**, **600B** can include a first chip **601** (also referred to herein as a bottom chip) and a second chip **651** (also referred to herein as a top chip).

[0032] First chip **601** can include a semiconductor substrate **602**. Semiconductor substrate **602** can be a monocrystalline silicon substrate or a substrate of any other suitable monocrystalline semiconductor material. First chip **601** can further include a first insulator layer **604** on semiconductor substrate **602**. First insulator layer **604** can be, for example, a silicon dioxide layer or a layer of any other suitable insulator material. Optionally, semiconductor substrate **602** can include a high resistance region **603** (also referred to herein as a trap-rich region) adjacent to first insulator layer **604**.

[0033] High resistance region **603** can be a defect region. This defect region can be polycrystalline or amorphous in structure and can include imperfections in the regular spacing of atoms that make up the semiconductor material. These imperfections form traps and, specifically, locations within the semiconductor substrate that restrict movement of charge carriers (i.e., electrons and holes) so that this defect region is referred to as being a trap-rich region. The presence of these imperfections or traps increases resistance so that this defect region is also referred to as a high resistance region. As discussed in greater detail below regarding the method embodiments, an exemplary technique for forming such a high resistance region **603** can include implantation of an inert dopant to modify substrate crystalline structure (e.g., to convert it to an amorphous structure). For purposes of this disclosure, an inert dopant refers to a dopant species that is generally not considered to be chemically reactive (i.e., that is neutral) at least with respect to the particular semiconductor material of the semiconductor substrate, that does not completely prevent recrystallization of the

doped region during a subsequent rapid thermal anneal process (RTA) (e.g., to create poly and/or monocrystalline region(s)), and that does not significantly impact the electrical properties of the resulting poly and/or monocrystalline region(s). Such inert dopants include, but are not limited to, inert gases (also referred to as noble gases) (e.g., argon, xenon, helium, neon, krypton, radon, etc.), silicon, or any other suitable inert dopant. The inert dopant implantation process is followed by a recrystallization anneal during which the amorphized portion begins to recrystallize from the top down and from the bottom up and, as a result, the defect region is formed. Thus, if semiconductor substrate **602** includes a high resistance region **603**, the inert dopant will be present below, within, and above the high resistance region **603**.

[0034] First chip **601** can include one of the transistors of one of the amplifiers (CE-A or CG-A) of LNA **100** on first insulator layer **604**. For example, first chip **601** can include NPN-type BJT **110** (as described in detail above) on first insulator layer **604** (e.g., see 3DIC **600A** of FIG. **6A**).

Alternatively, first chip **601** can include PFET **120** (as described in detail above) on first insulator layer **604** (e.g., see 3DIC **600B** of FIG. **6B**). Isolation regions **606** (e.g., shallow trench isolation (STI) regions) can be on first insulator layer **604** positioned laterally adjacent to the transistor.

[0035] First chip **601** can include multiple first dielectric material layers **607**. First dielectric material layers **607** can include one or more first dielectric material layers in a first MOL region **610** adjacent to STI regions **606** and further over first front end of the line (FEOL) devices on first insulator layer **604**, including either NPN-type BJT **110** (as in FIG. **6A**) or PFET **120** (as in FIG. **6B**). The first MOL region **610** can further include first contacts extending therethrough to the first FEOL device(s). The first dielectric material layers **607** can further include multiple first dielectric material layers in a first BEOL region **620** (including first BEOL metal levels therein) adjacent to first MOL region **610**.

[0036] Second chip **651** can include a second insulator layer **654**. Second insulator layer **654** can be, for example, a silicon dioxide layer or a layer of any other suitable insulator material. Second chip **651** can include one of the transistors of LNA **100** on second insulator layer **654**. For example, if first chip **601** includes NPN-type BJT **110** on first insulator layer **604**, then second chip **651** can include PFET **120** on second insulator layer **654** (e.g., see 3DIC **600A** of FIG. **6A**). Alternatively, if first chip **601** includes PFET **120** on first insulator layer **604**, then second chip **651** can include NPN-type BJT **110** on second insulator layer **654** (e.g., see 3DIC **600B** of FIG. **6B**). Isolation regions **656** (e.g., shallow trench isolation (STI) regions) can be below and immediately adjacent to second insulator layer **654**, and hence laterally adjacent to the transistor.

[0037] Second chip **651** can include multiple second dielectric material layers **657**. Second dielectric material layers **657** can include one or more second dielectric material layers in a second MOL region **660** adjacent to STI regions **656** and further extend below second FEOL devices, including either PFET **120** (as in FIG. **6A**) or NPN-type BJT **110** (as in FIG. **6B**). The second MOL region **660** can further include second contacts extending therethrough to the second FEOL device(s). The second dielectric material layers **657** can further include multiple second dielectric material layers in a second BEOL region **670** (including second BEOL metal levels therein) adjacent to second MOL region **660**.

[0038] Second chip **651** can further be flipped relative to first chip **601** and outermost surfaces of BEOL regions **620**, **670** of the two chips **601**, **651** can be bonded together or otherwise connected (see bonded surfaces **680**). Specifically, bonded surfaces **680** can be physically attached to each other and can have bonding elements in electrical communication with each other.

[0039] In these embodiments, at least some of the passive devices mentioned above (including, but not limited to, inductors **130**, **115**, **117** and **125** and capacitors **116**, **127**, and **128**) can be included in the BEOL regions **620** and/or **670** between NPN-type BJT **110** and PFET **120**. Optionally, one or more of these passive devices could have portions included in BEOL region **620** of first chip **601** and BEOL region **670** of second chip **651**. For example, any of the inductors **130**, **115**, **117**, and/or **125** and any of capacitors **116**, **127**, and/or **128** could have a first portion, which is in BEOL region

620 of first chip **601** and a second portion, which is in BEOL region **670** of second chip **651**, stacked above, and connected in parallel to the first portion. By stacking different portions of passive device(s) in the BEOL regions of chips **601** and **651** of 3DIC **600A** or **600B** and further connecting them in parallel, 3DIC area is reduced. Furthermore, by specifically stacking different portions of any inductor in the BEOL regions of chips **601** and **651** a relatively high quality factor (also referred to as a high-Q) can be achieved. Those skilled in the art will recognize the quality factor (Q) of an inductor refers the ratio of its inductive reactance to its resistance at a given frequency and is a measure of its efficiency. The higher the Q factor of the inductor, the closer it approaches the behavior of an ideal inductor.

[0040] For purposes of illustration, base inductor **117** is shown as including a first portion **117.1** in a top (thickest) metal level of BEOL region **620** and a second portion **117.2** within top (thickest) metal level of BEOL region **670**. Second portion **117.2** can be aligned above first portion **117.1** and can further be connected in parallel to first portion **117.1** (e.g., by vias bonded together at bonded surfaces **680**). First portion **117.1** and second portion **117.2** can have the same dimensions (e.g., same wire thickness (height), same wire width, same wire length, etc.). Alternatively, first portion **117.1** and second portion **117.2** can have different dimensions (e.g., different wire thicknesses, etc.). In any case, by including the two portions **117.1** and **117.2** thick metal levels, stacking them, and connecting them in parallel, base inductor **117** has a high-Q.

[0041] Any of inductors **130**, **115**, **117**, and/or **125** can have uniform wire widths between their respective end terminals (e.g., as shown in FIGS. **4A-1** or **4B-1**) or can have tapered wire widths from the outer end terminal to the inner end terminal (e.g., as shown in FIGS. **4A-2** or **4B-2**). For purposes of illustration, base inductor **117** is specifically shown in FIGS. **6A** and **6B** as being a tapered spiral inductor. In this case, the wire widths of first and second portions **117.1-117.2** decrease from their respective outer ends to their respective inner ends. As mentioned above, base inductor **117** extends between input node **101** and base **113** of NPN-BJT **110**. By forming this base inductor **117** as a tapered spiral inductor, the noise factor of the LNA **100** can be maintained at a relatively low level between 0.5 dB and 1.0 dB (e.g., an NF of 0.7 dB).

[0042] Resistor **126** can be, for example, a thin film resistor included within a BEOL region (as illustrated). Alternatively, resistor **126** could be included within a MOL region (e.g., an undoped or low-doped polysilicon resistor or any other now known or subsequently developed MOL resistor) or included within as a FEOL device (e.g., an undoped or low-doped monocrystalline silicon resistor or any other now know or subsequently developed FEOL resistor). Required electrical connections between the LNA components can include a combination of contacts in MOL regions **610**, **660** and vias/metal wires in BEOL regions **620**, **670**.

[0043] FIGS. **6A** and **6B** are provided to illustrate NPN-BJT **110** of CE-A and PFET **120** of CG-A of LNA **100** on different chips **601**, **651** of a 3DIC and to further show that the various passive devices of CE-A and CG-A can be included within the interlayer dielectric material and metal levels between CE-A and CG-A of LNA **100** (i.e., MOL region **610**, BEOL region **620**, BEOL region **670**, and/or MOL region **660**). FIGS. **6A** and **6B** are not intended to be limiting. It should be understood that in order to meet required performance specifications and to comply with design rules for the particular technology node at issue the various passive devices described above and connected to NPN-type BJT **110** and PFET **120** can be placed at different levels and/or at different locations within MOL and BEOL regions, can have different sizes, can have different configurations, etc. as compared to the passive devices illustrated.

[0044] Also disclosed herein are method embodiments for forming the 3DIC structures **600A** and **600B** described above and illustrated in FIGS. **6A** and **6B**, respectively. FIGS. **7.1-7.3** described below illustrate specifically formation of the 3DIC structure **600A** of FIG. **6A** wherein NPN-type BJT **110** is formed on a first chip **601** and PFET **120** is formed on a second chip **651**. However, essentially the same process steps could be employed to form the 3DIC **600B** of FIG. **6B** except that PFET **120** would be formed on first chip **601** and NPN-type BJT **110** would be formed on

second chip **651**.

[0045] The methods can include forming a first chip (e.g., see first chip **601** in FIG. **7.1**).

Formation of the first chip **601** can begin with a first semiconductor-on-insulator structure. The first semiconductor-on-insulator structure can be, for example, a silicon-on-insulator (SOI) structure including: a first semiconductor substrate **602**; a first insulator layer **604** on the first semiconductor substrate **602**; and a first semiconductor layer **605** on the first insulator layer **604**.

[0046] First FEOL devices, including either NPN-type BJT **110** or PFET **120**, with STI regions **606** positioned laterally thereto can be formed on first insulator layer **604** using the first semiconductor layer **605**. As mentioned above, the method is described herein with an NPN-type BJT **110** being formed on first chip **601**. The NPN-type BJT **110** shown in FIG. **7.1** is a semiconductor-on-insulator, symmetric, lateral, NPN-type heterojunction bipolar transistor (HBT) (also referred to herein as a SiGe NPN-type BJT). However, it should be understood that FIG. **7.1** is not intended to be limiting. Alternatively, the NPN-type BJT **110** formed on first chip **601** could be a standard BJT as opposed to an HBT (as illustrated), a vertical device as opposed to a lateral device (as illustrated), an asymmetric device as opposed to a symmetric device (as illustrated), etc. In any case, as illustrated in FIG. **7.1**, NPN-type BJT **110** can be formed so as to include at least emitter and collector regions **111** and **112** and a base region **113** positioned between emitter and collector regions **111** and **112**. Techniques for forming such NPN-type BJTs with various different configurations are well known in the art. Thus, the details thereof have been omitted from this specification in order to allow the reader to focus on the salient aspects of LNA **100** (including inclusion of both a CE-A with an NPN-type BJT and various passive devices, a CG-A with a PFET and various passive devices, a common inductor, and the connections therebetween implemented, for example, on a 3DIC).

[0047] MOL and BEOL processing can then be performed. Such processing can include, but is not limited to: formation of first dielectric material layers **607** (including first dielectric material layer(s) in a first MOL region **610** and first dielectric material layers in a first BEOL region **620** on first MOL region **610**); formation of first contacts extending through first MOL region **610** to terminals of NPN-type BJT **110**; formation of first passive devices or portions thereof as described above (e.g., formation of inductor **115**, capacitor **116**, and first portion **117.1** of inductor **117**; optional formation of common inductor **130**; and formation of any required connections (as indicated in FIG. **1**) to each other and to NPN-type BJT **110**. It should be understood that the various first dielectric materials layers **607** are formed throughout such processing as MOL features (e.g., MOL contacts) and BEOL metal features are formed therein. Such MOL and BEOL processing techniques, including techniques for forming passive devices such as inductors, capacitors, and resistors, are well known. Thus, the details thereof have been omitted from this specification in order to allow the reader to focus on the salient aspects of LNA **100** (including inclusion of both a CE-A with an NPN-type BJT and various passive devices, a CG-A with a PFET and various passive devices, a common inductor, and the connections therebetween implemented, for example, on a 3DIC).

[0048] The methods can also include formation a second chip (e.g., see second chip **651** in FIG. **7.2**). Formation of the second chip **651** can begin with a second semiconductor-on-insulator structure. The second semiconductor-on-insulator structure can be, for example, a silicon-on-insulator (SOI) structure including: a second semiconductor substrate **652** (also referred to herein as a sacrificial semiconductor substrate); a second insulator layer **654** on the second semiconductor substrate **652**; and a second semiconductor layer **655** on second insulator layer **654**.

[0049] Second FEOL devices, including PFET **120** if NPN-type BJT **110** is formed on first chip **601** or vice versa, and STI regions **656** positioned laterally thereto can be formed on second insulator layer **656** using the second semiconductor layer **655**. As mentioned above, the method is described herein with an NPN-type BJT **110** being formed on first chip **601**, so a PFET **120** is formed on second chip **651**. The PFET **120** shown in FIG. **7.2** is a semiconductor-on-insulator,

symmetric, planar PFET. However, it should be understood that FIG. 7.2 is not intended to be limiting. Alternatively, the PFET **120** formed on second chip **651** could be a bulk semiconductor structure as opposed to a semiconductor-on-insulator structure (as illustrated), a non-planar PFET as opposed to a planar PFET (as illustrated), a multi-gate finger PFET as opposed to a single gate PFET (as illustrated), an asymmetric PFET as opposed to a symmetric PFET (as illustrated), etc. In any case, as illustrated in FIG. 7.2, PFET **120** can be formed so as to include a source region **121** and a drain region **122**, a channel region **123** between source and drain regions **121** and **122**, and a gate **124** adjacent to the channel region **123**. Techniques for forming such PFETs with various different configurations are well known. Thus, the details thereof have been omitted from this specification in order to allow the reader to focus on the salient aspects of LNA **100** (including inclusion of both a CG-A with an NPN-type BJT and various passive devices, a CG-A with a PFET and various passive devices, a common inductor, and the connections therebetween implemented, for example, on a 3DIC).

[0050] MOL and BEOL processing can then be performed. Such processing can include, but is not limited to: formation of second dielectric material layers **657** (including second dielectric material layer(s) in a second MOL region **660** and second dielectric material layers in a second BEOL region **670** on second MOL region **660**); formation of second contacts extending through second MOL region **660** to terminals of PFET **120**; formation of second passive devices or portions thereof described above (e.g., inductor **125**, capacitors **127** and **128**, resistor **126**, and second portion **117.2** of inductor **117**); optionally, formation of common inductor **130** (e.g., if not formed on first chip **601**); and formation of any required connections (as indicated in FIG. 1) to each other and to PFET **120**. It should be understood that the various second dielectric materials layers **657** are formed throughout such processing as MOL features (e.g., MOL contacts) and BEOL metal features are formed therein. Such MOL and BEOL processing techniques, including techniques for forming passive devices, such as inductors, capacitors and resistors, are well known. Thus, the details thereof have been omitted from this specification in order to allow the reader to focus on the salient aspects of LNA **100** (including inclusion of both a CE-A with an NPN-type BJT and various passive devices, a CG-A with a PFET and various passive devices, a common inductor, and the connections therebetween implemented, for example, on a 3DIC).

[0051] The methods can further include flipping second chip **651** relative to first chip **601** and stacking second chip **651** on first chip **601** so that outermost surfaces of first dielectric material layers **607** (distal to first FEOL devices, such as NPN-type BJT **110**, on first chip **601**) and second dielectric material layers **657** (distal to second FEOL devices, such as PFET **120**, on second chip **651**) are immediately adjacent to each other (see FIG. 7.3). It should be noted that, during BEOL processing on first chip **601** and on second chip **651**, patterning of one or more features (e.g., different portions **130.1** and **130.2** of common inductor **130**, of vias, etc.) can be performed so that, when second chip **651** is flipped relative to and stacked on first chip **601** these features will be vertically aligned. Then, the outermost surfaces of first dielectric material layers **607** and second dielectric material layers **657** can be bonded together (see bonded outermost surfaces **680**).

[0052] Bonding can, for example, be performed using a hybrid bonding technique (e.g., a direct bond interconnect (DBI) techniques. Specifically, a hybrid bonding technique can be performed, resulting in dielectric-to-dielectric bonding of adjacent dielectric materials (e.g., of the first and second dielectric material layers) and metal-to-metal bonding (e.g., copper-to-copper bonding) of the adjacent metal materials (e.g., of different portions **130.1** and **130.2** of common inductor **130**, of vertically aligned vias, etc.). Such hybrid bonding techniques are well known in the art. Thus, a detailed discussion thereof has been omitted from this specification in order to allow the reader to focus on the salient aspects of the disclosed embodiments. However, those skilled in the art will recognize that such techniques typically rely on application of both pressure and relatively high heat. Alternatively, any other suitable wafer-to-wafer, chip-to-wafer, or chip-to-chip bonding technique could be employed (e.g., bump-type bonding techniques).

[0053] The methods can further include removing second semiconductor substrate **652** (i.e., the sacrificial semiconductor substrate) to expose second insulator layer **654** (see FIG. **6A**). Removal of second semiconductor substrate **652** can be achieved, for example, using a grinding process or any other suitable process. Substrate grinding techniques are well known in the art and, thus, the details thereof have been omitted from this specification in order to allow the reader to focus on the salient aspects of the disclosed embodiments.

[0054] The methods can further include additional processing to complete the 3DIC structure. This additional processing can include, but is not limited to, the following: forming an additional insulator layer on exposed surface of second insulator layer **654** (e.g., by thermal oxide deposition, chemical vapor deposition (CVD), or any other suitable insulator deposition process); optionally, performing a polishing process (e.g., a chemical mechanical polishing (CMP) process); forming through oxide vias (TOVs); forming input/output pads on the TOVs, etc.

[0055] In the method and structures described above, a semiconductor material refers to a material whose conducting properties can be altered by doping with an impurity. Exemplary semiconductor materials include, for example, silicon-based semiconductor materials (e.g., silicon, silicon germanium, silicon germanium carbide, silicon carbide, etc.) and III-V compound semiconductors (i.e., compounds obtained by combining group III elements, such as aluminum (Al), gallium (Ga), or indium (In), with group V elements, such as nitrogen (N), phosphorous (P), arsenic (As) or antimony (Sb)) (e.g., GaN, InP, GaAs, or GaP). A pure semiconductor material and, more particularly, a semiconductor material that is not doped with an impurity for the purposes of increasing conductivity (i.e., an undoped semiconductor material) is referred to in the art as an intrinsic semiconductor. A semiconductor material that is doped with an impurity for the purposes of increasing conductivity (i.e., a doped semiconductor material) is referred to in the art as an extrinsic semiconductor and will be more conductive than an intrinsic semiconductor made of the same base material. That is, extrinsic silicon will be more conductive than intrinsic silicon; extrinsic silicon germanium will be more conductive than intrinsic silicon germanium; and so on. Furthermore, it should be understood that different impurities (i.e., different dopants) can be used to achieve different conductivity types (e.g., P-type conductivity and N-type conductivity) and that the dopants may vary depending upon the different semiconductor materials used. For example, a silicon-based semiconductor material (e.g., silicon, silicon germanium, etc.) is typically doped with a Group III dopant, such as boron (B) or indium (In), to achieve P-type conductivity, whereas a silicon-based semiconductor material is typically doped with a Group V dopant, such as arsenic (As), phosphorous (P) or antimony (Sb), to achieve N-type conductivity. A gallium nitride (GaN)-based semiconductor material is typically doped with magnesium (Mg) to achieve P-type conductivity and with silicon (Si) or oxygen to achieve N-type conductivity. Those skilled in the art will also recognize that different conductivity levels will depend upon the relative concentration levels of the dopant(s) in a given semiconductor region.

[0056] The terminology used herein is for the purpose of describing the disclosed structures and methods and is not intended to be limiting. For example, as used herein, the singular forms “a,” “an,” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. Additionally, as used herein, the terms “comprises,” “comprising,” “includes,” and/or “including” specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof. Furthermore, as used herein, terms such as “right,” “left,” “vertical,” “horizontal,” “top,” “bottom,” “upper,” “lower,” “under,” “below,” “underlying,” “over,” “overlying,” “parallel,” “perpendicular,” etc., are intended to describe relative locations as they are oriented and illustrated in the drawings (unless otherwise indicated) and terms such as “touching,” “in direct contact,” “abutting,” “directly adjacent to,” “immediately adjacent to,” etc., are intended to indicate that at least one element physically contacts another element (without other elements separating the described elements). The term

“laterally” is used herein to describe the relative locations of elements and, more particularly, to indicate that an element is positioned to the side of another element as opposed to above or below the other element, as those elements are oriented and illustrated in the drawings. For example, an element that is positioned laterally adjacent to another element will be beside the other element, an element that is positioned laterally immediately adjacent to another element will be directly beside the other element, and an element that laterally surrounds another element will be adjacent to and border the outer sidewalls of the other element. The corresponding structures, materials, acts, and equivalents of all means or step plus function elements in the claims below are intended to include any structure, material, or act for performing the function in combination with other claimed elements as specifically claimed.

[0057] The method as described above is used in the fabrication of integrated circuit chips. The resulting integrated circuit chips can be distributed by the fabricator in raw wafer form (that is, as a single wafer that has multiple unpackaged chips), as a bare die, or in a packaged form. In the latter case the chip is mounted in a single chip package (such as a plastic carrier, with leads that are affixed to a motherboard or other higher level carrier) or in a multichip package (such as a ceramic carrier that has either or both surface interconnections or buried interconnections). In any case the chip is then integrated with other chips, discrete circuit elements, and/or other signal processing devices as part of either (a) an intermediate product, such as a motherboard, or (b) an end product. The end product can be any product that includes integrated circuit chips, ranging from toys and other low-end applications to advanced computer products having a display, a keyboard or other input device, and a central processor.

[0058] The descriptions of the various disclosed embodiments have been presented for purposes of illustration but are not intended to be exhaustive or limiting. Many modifications and variations will be apparent to those of ordinary skill in the art without departing from the scope and spirit of the disclosed embodiments. The terminology used herein was chosen to best explain the principles of the embodiments, the practical application or technical improvement over technologies found in the marketplace, or to enable others of ordinary skill in the art to understand the embodiments disclosed herein.

Claims

1. A structure including: a bipolar junction transistor including: a base region connected to an input node; and a collector region; and a field effect transistor including: a source region connected to the collector region; and a drain region connected to an output node.
2. The structure of claim 1, wherein the bipolar junction transistor and the field effect transistor are on different chips of a three-dimensional integrated circuit and wherein interlayer dielectric material and metal levels of the different chips are between the bipolar junction transistor and the field effect transistor.
3. The structure of claim 1, wherein the bipolar junction transistor further includes an emitter region, and wherein the structure further includes: an emitter-base capacitor connected between the emitter region and the base region; an emitter inductor connected between the emitter region and ground; and a base inductor connected between the input node and the base region.
4. The structure of claim 3, wherein the base inductor is a tapered spiral inductor.
5. The structure of claim 1, wherein the field effect transistor further includes: a channel region between the source region and the drain region; and a gate adjacent to the channel region and connected to a bias voltage node, and wherein the structure further includes: a gate resistive element connected between the gate and the bias voltage node; a gate capacitor connected between the gate and ground; an output capacitor connected between the drain region and the output node; and a drain inductor connected between the drain region and ground.
6. The structure of claim 1, wherein the bipolar junction transistor is an NPN-type bipolar junction

transistor and the base region includes silicon germanium and wherein the field effect transistor is a P-channel field effect transistor with a silicon active device region.

7. The structure of claim 1, further comprising a common inductor connected at one end to a positive voltage rail and at an opposite end to the collector region of the bipolar junction transistor and the source region of the field effect transistor.

8. A structure including: a bipolar junction transistor on a first chip, wherein the bipolar junction transistor includes a base region connected to an input node and a collector region; and a field effect transistor on a second chip, wherein the second chip is stacked on the first chip and wherein the field effect transistor includes: a source region connected to the collector region and a drain region connected to an output node.

9. The structure of claim 8, wherein the first chip includes first metal levels and the second chip includes second metal levels adjacent to the first metal levels, wherein the structure further includes passive elements, and wherein at least some of the passive elements are in the first metal levels and the second metal levels between the bipolar junction transistor and the field effect transistor.

10. The structure of claim 9, wherein the bipolar junction transistor further includes an emitter region, and wherein the passive elements include: an emitter-base capacitor connected between the emitter region and the base region; an emitter inductor connected between the emitter region and ground; and a base inductor connected between the input node and the base region.

11. The structure of claim 10, wherein the base inductor is a tapered spiral inductor with a first portion on the first chip and a second portion connected in parallel to the first portion and on the second chip.

12. The structure of claim 9, wherein the field effect transistor further includes: a channel region between the source region and the drain region; and a gate adjacent to the channel region and connected to a bias voltage node, and wherein the passive elements include: a gate resistive element connected between the gate and the bias voltage node; a gate capacitor connected between the gate and ground; an output capacitor connected between the drain region and the output node; and a drain inductor connected between the drain region and ground.

13. The structure of claim 9, wherein the passive elements further include a common inductor connected at one end to a positive voltage rail and at an opposite end to the collector region of the bipolar junction transistor and the source region of the field effect transistor.

14. The structure of claim 8, wherein the bipolar junction transistor is an NPN-type bipolar junction transistor and the base region includes silicon germanium and wherein the field effect transistor is a P-channel field effect transistor with a silicon active device region.

15. A structure including: a field effect transistor on a first chip; and a bipolar junction transistor on a second chip, wherein the second chip is stacked on the first chip, wherein the bipolar junction transistor includes a base region connected to an input node and a collector region, and wherein the field effect transistor includes: a source region connected to the collector region and a drain region connected to an output node.

16. The structure of claim 15, wherein the first chip includes first metal levels and the second chip includes second metal levels adjacent to the first metal levels, wherein the structure further includes passive elements, and wherein at least some of the passive elements are in the first metal levels and the second metal levels between the field effect transistor and the bipolar junction.

17. The structure of claim 16, wherein the bipolar junction transistor further includes an emitter region, and wherein the passive elements include: an emitter-base capacitor connected between the emitter region and the base region; an emitter inductor connected between the emitter region and ground; and a spiral base inductor connected between the input node and the base region, wherein the spiral base inductor has a first portion on the first chip and a second portion connected in parallel to the first portion and on the second chip.

18. The structure of claim 16, wherein the field effect transistor further includes: a channel region between the source region and the drain region; and a gate adjacent to the channel region and

connected to a bias voltage node, and wherein the passive elements include: a gate resistive element connected between the gate and the bias voltage node; a gate capacitor connected between the gate and ground; an output capacitor connected between the drain region and the output node; and a drain inductor connected between the drain region and ground.

19. The structure of claim 16, wherein the passive elements further include a common inductor connected at one end to a positive voltage rail and at an opposite end to the collector region of the bipolar junction transistor and the source region of the field effect transistor.

20. The structure of claim 15, wherein the field effect transistor is a P-channel field effect transistor with a silicon active device region, and wherein the bipolar junction transistor is an NPN-type bipolar junction transistor and the base region includes silicon germanium.
